

Product data sheet

1. General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a leadless ultra small DFN1006D-2 (SOD882D) Surface-Mounted Device (SMD) plastic package with visible and solderable side pads.

2. Features and benefits

- Average forward current: I_{F(AV)} ≤ 1 A
- Reverse voltage: V_R ≤ 20 V
- Low forward voltage $V_F \le 490 \text{ mV}$
- AEC-Q101 qualified
- Ultra small and leadless SMD plastic package
- Solderable side pads
- Package height typ. 0.37 mm

3. Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- Reverse polarity protection
- Low power consumption applications
- Ultra high-speed switching
- LED backlight for mobile application

4. Quick reference data

Table 1. Quick reference data							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I _{F(AV)}	average forward current	δ = 0.5 ; f = 20 kHz; T _{sp} ≤ 130 °C; square wave		-	-	1	A
		δ = 0.5 ; f = 20 kHz; T _{amb} ≤ 80 °C; square wave	[1]	-	-	1	A
V _R	reverse voltage	T _j = 25 °C		-	-	20	V
V _F	forward voltage	I_F = 1 A; pulsed; t_p \leq 300 μ s; δ \leq 0.02 $\ ;$ T_j = 25 °C		-	428	490	mV
I _R	reverse current	V _R = 10 V; T _j = 25 °C		-	28	50	μA





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Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
t _{rr}	reverse recovery time	$I_F = 0.5 \text{ A}; I_R = 0.5 \text{ A}; I_{R(meas)} = 0.1 \text{ A};$	-	1.6	-	ns
		T _j = 25 °C				

[1] Device mounted on a ceramic PCB, AI_2O_3 , standard footprint.

5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	К	cathode[1]		1 🛃 2
2	А	anode		sym001
			Transparent top view	
			DFN1006D-2 (SOD882D)	

[1] The marking bar indicates the cathode.

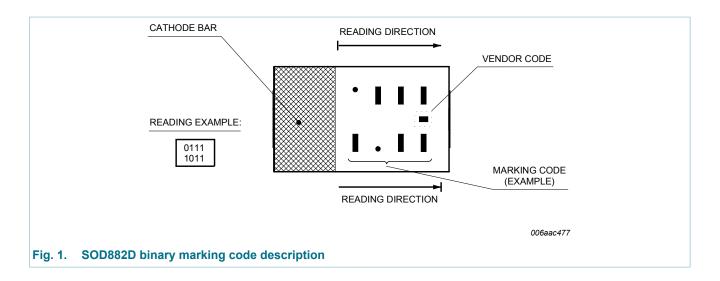
6. Ordering information

Table 3. Ordering in	formation				
Type number	Package				
	Name	Description	Version		
PMEG2010BELD	DFN1006D-2	DFN1006D-2: leadless ultra small plastic package; 2 terminals	SOD882D		

7. Marking

Table 4. Marking codes	
Type number	Marking code
PMEG2010BELD	0000 1001

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Мах	Unit
V _R	reverse voltage	T _j = 25 °C		-	20	V
l _F	forward current	T _{sp} ≤ 130 °C		-	1	А
I _{F(AV)}	average forward current	δ = 0.5 ; f = 20 kHz; T _{sp} ≤ 130 °C; square wave		-	1	A
		δ = 0.5 ; f = 20 kHz; T _{amb} ≤ 80 °C; square wave	[1]	-	1	A
I _{FRM}	repetitive peak forward current	t _p ≤ 1 ms; δ ≤ 0.25		-	3	А
I _{FSM}	non-repetitive peak forward current	t_p = 8 ms; $T_{j(init)}$ = 25 °C; square wave		-	6	A
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[2][3]	-	370	mW
			[4][3]	-	735	mW
			[1][3]	-	1135	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[3] Reflow soldering is the only recommended soldering method.

 [4] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for cathode 1 cm².

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Thermal characteristics 9.

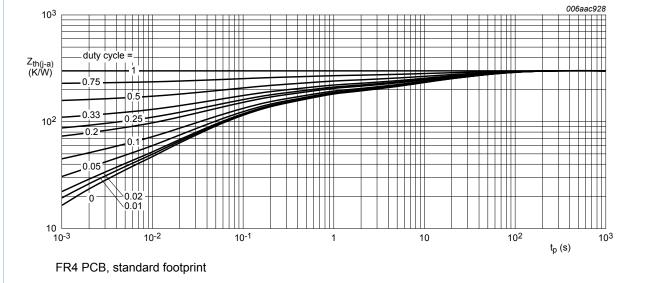
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance	in free air	[1][2][3]	-	-	340	K/W
	from junction to ambient		[1][4][3]	-	-	170	K/W
	ampient		[1][5][3]	-	-	110	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		[6]	-	-	25	K/W

[1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses.

Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint. [2]

Reflow soldering is the only recommended soldering method. [3]

- [4] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².
- [5] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.
- [6] Soldering point of cathode tab.

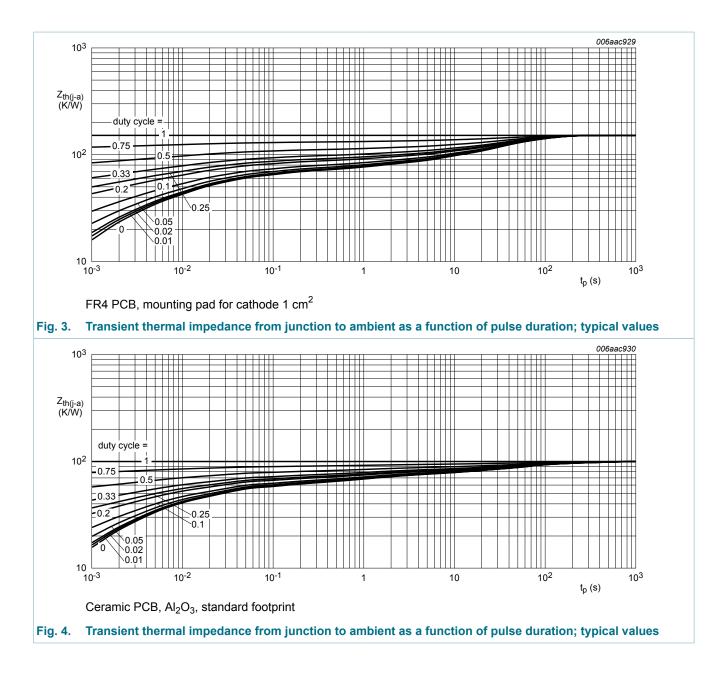


Transient thermal impedance from junction to ambient as a function of pulse duration; typical values Fig. 2.

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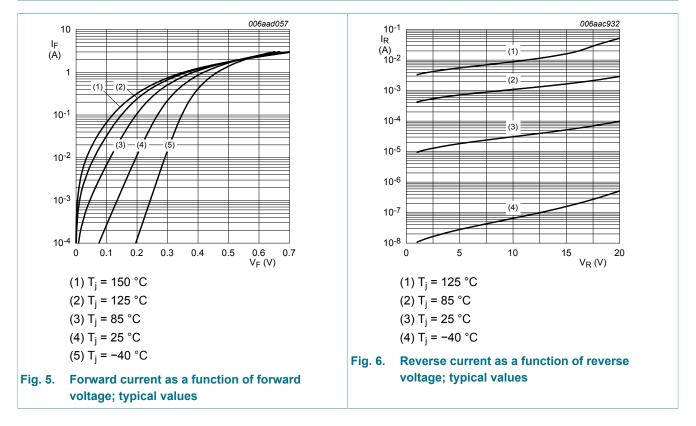
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10. Characteristics

	haracteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
VF	forward voltage	$\begin{array}{l} I_{\text{F}} = 100 \text{ mA; pulsed; } t_{p} \leq 300 \mu\text{s;} \\ \overline{\delta} \leq 0.02 \ \ ; T_{j} = 25 \ ^{\circ}\text{C} \end{array}$	-	266	310	mV
		$\label{eq:lf} \begin{array}{l} I_{\text{F}} = 500 \text{ mA; pulsed; } t_{p} \leq 300 \mu\text{s;} \\ \delta \leq 0.02 ; T_{j} = 25 \ ^{\circ}\text{C} \end{array}$	-	353	390	mV
		I _F = 1 A; pulsed; t _p ≤ 300 μs; δ ≤ 0.02 ; T _j = 25 °C	-	428	490	mV
I _R	reverse current	V _R = 10 V; T _j = 25 °C	-	28	50	μA
		V _R = 20 V; T _j = 25 °C	-	87	200	μA
C _d	diode capacitance	V _R = 1 V; f = 1 MHz; T _j = 25 °C	-	31	40	pF
t _{rr}	reverse recovery time	$I_F = 0.5 \text{ A}; I_R = 0.5 \text{ A}; I_{R(meas)} = 0.1 \text{ A};$ $T_j = 25 \text{ °C}$	-	1.6	-	ns
V _{FRM}	peak forward recovery voltage	I _F = 0.5 A; dI _F /dt = 20 A/μs; T _j = 25 °C	-	565	-	mV

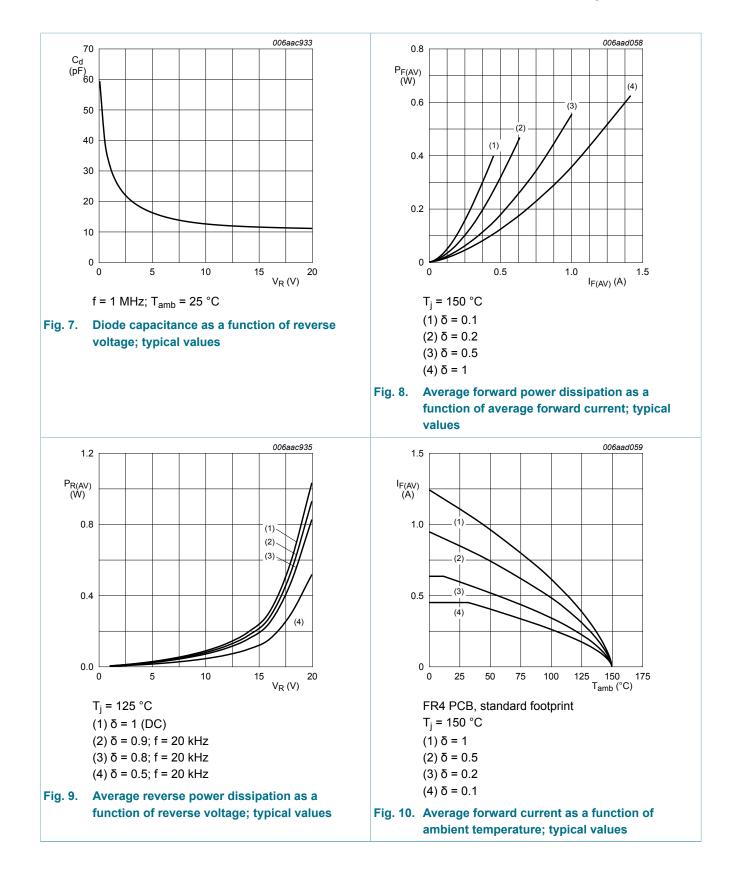


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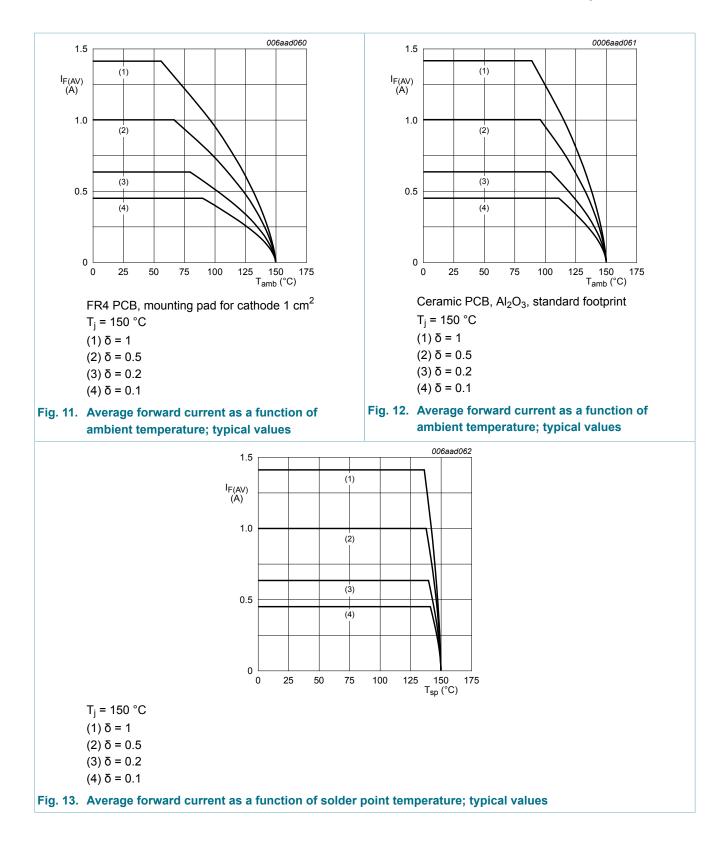
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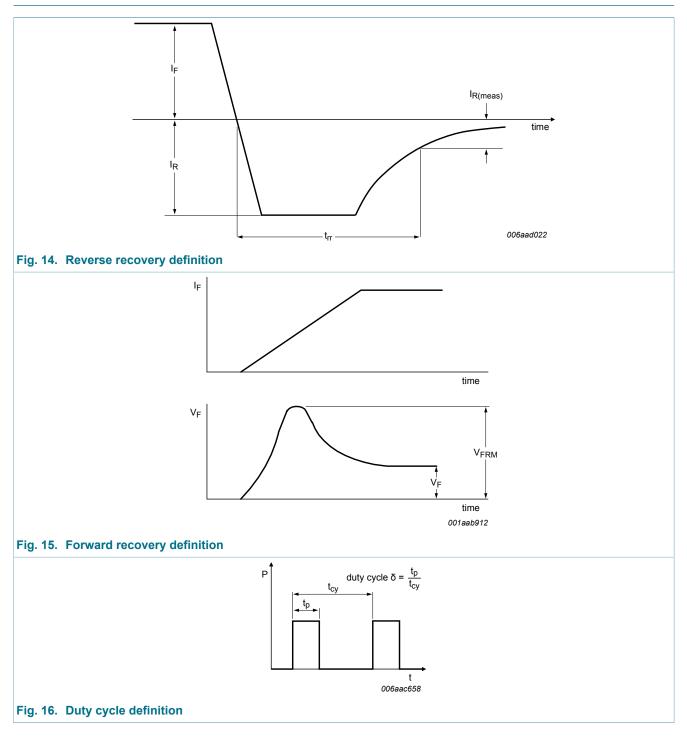


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11. Test information



The current ratings for the typical waveforms are calculated according to the equations: $I_{F(AV)} = I_M \times \delta$ with I_M defined as peak current, $I_{RMS} = I_{F(AV)}$ at DC, and $I_{RMS} = I_M \times \sqrt{\delta}$ with I_{RMS} defined as RMS current.

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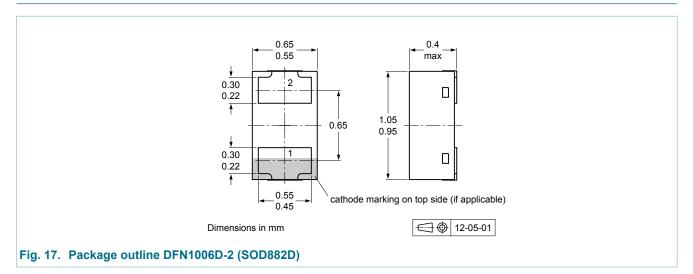
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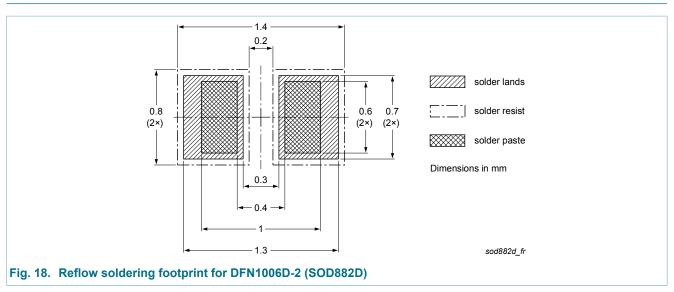
11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

12. Package outline



13. Soldering



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14. Revision history

Table 8. Revision his	story			
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMEG2010BELD v.2	20150804	Product data sheet -		PMEG2010BELD v.1
Modifications:	Section Marking: up	dated figure 1.	·	
PMEG2010BELD v.1	20120418	Product data sheet	-	-

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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